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### (54) TSV SEMICONDUCTOR DEVICE INCLUDING INDUCTIVE COMPENSATION **LOOPS**

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#### (57)**ABSTRACT**

A semiconductor device includes semiconductor dies formed with through silicon vias (TSVs). The TSVs are coupled to contact pads in a surface of the semiconductor die by coils forming inductance loops at a number of contact pads. These inductance loops serve to distribute the capacitance at each bond pad along transmission lines, which distribution of the capacitance allows for a marked increase in read/write bandwidth for the semiconductor die.

